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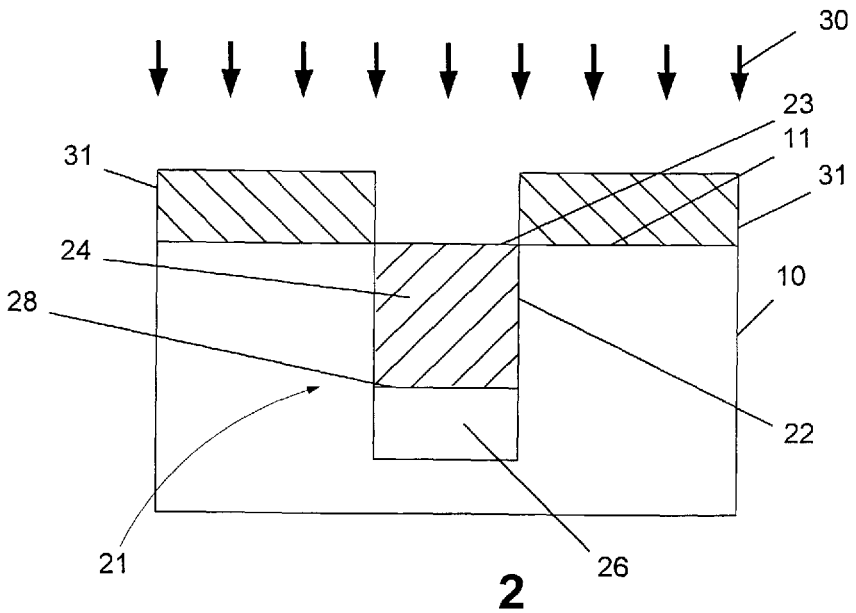
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(54) Title: METHOD OF CONTROLLING WELL LEAKAGE FOR TRENCH ISOLATIONS OF DIFFERING DEPTHS



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(57) Abstract: A method comprising forming a trench (22) in a semiconducting substrate (10) and forming an isolation material (24) in said trench (22). The method further comprises determining at least one of the depth of said trench (22) and the thickness of said trench isolation material (24) and determining an energy level for an ion implantation process to be performed through said isolation material (24) based upon at least one of said determined depth of said trench (22) and said determined thickness of said isolation material (24).

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